

Standard Rectifier Module

$$V_{RRM} = 2 \times 800 \text{ V}$$

$$I_{FAV} = 59 \text{ A}$$

$$V_F = 1.26 \text{ V}$$

Phase leg

Part number

MDD44-08N1B



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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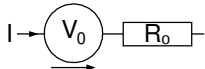
Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				800	V
I_R	reverse current	$V_R = 800\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			100	μA
		$V_R = 800\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			10	mA
V_F	forward voltage drop	$I_F = 100\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.30	V
		$I_F = 200\text{ A}$				1.60	V
		$I_F = 100\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.26	V
		$I_F = 200\text{ A}$				1.67	V
I_{FAV}	average forward current	$T_C = 100^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$			59	A
$I_{F(RMS)}$	RMS forward current	180° sine				100	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.80	V
r_F	slope resistance					4.3	m Ω
R_{thJC}	thermal resistance junction to case					0.59	K/W
R_{thCH}	thermal resistance case to heatsink				0.2		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			212	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			1.15	kA
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.24	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			980	A
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			1.06	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}\text{C}$			6.62	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			6.40	kA ² s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}\text{C}$			4.80	kA ² s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0\text{ V}$			4.63	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		27		pF

Package TO-240AA				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal				200	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		125	°C
Weight					76		g
M_D	mounting torque			2.5		4	Nm
M_T	terminal torque			2.5		4	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7			mm
$d_{Spb/Apb}$		terminal to backside	16.0	16.0			mm
V_{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4800			V
		t = 1 minute		4000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD44-08N1B	MDD44-08N1B	Box	36	457973

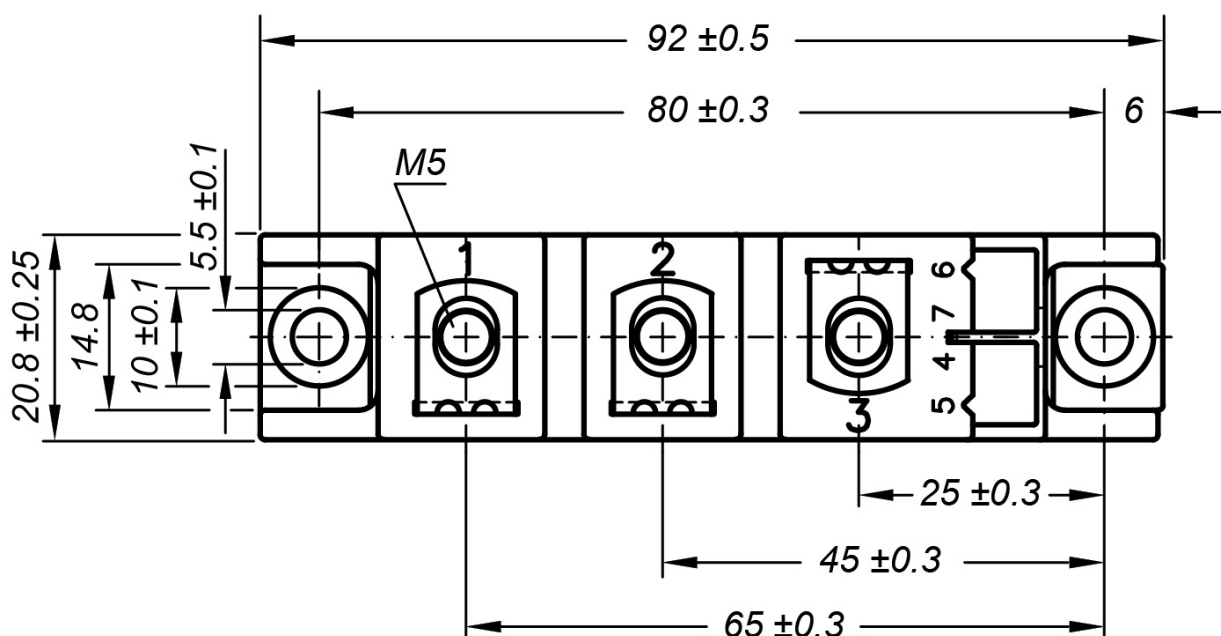
Similar Part	Package	Voltage class
MDD44-12N1B	TO-240AA	1200
MDD44-14N1B	TO-240AA	1400
MDD44-16N1B	TO-240AA	1600
MDD44-18N1B	TO-240AA	1800

Equivalent Circuits for Simulation			$T_{VJ} = 150^{\circ}\text{C}$
			
$V_{0\max}$	threshold voltage	0.8	V
$R_{0\max}$	slope resistance *	3.1	mΩ

Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“



Rectifier

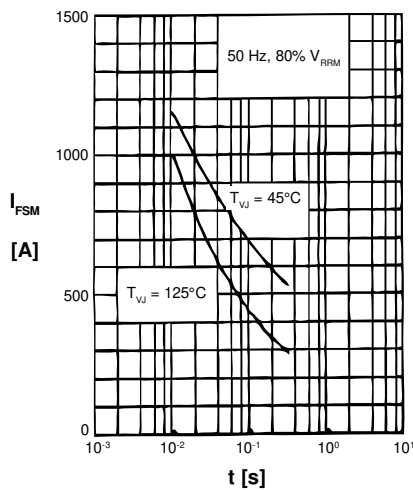


Fig. 1 Surge overload current
 I_{TSM} , I_{FSM} : Crest value, t : duration

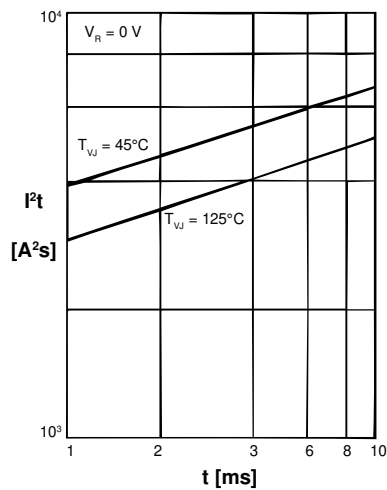


Fig. 2 I^2t versus time (1-10 ms)

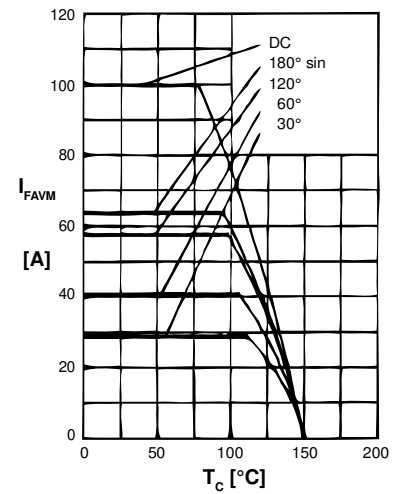


Fig. 3 Maximum forward current at case temperature

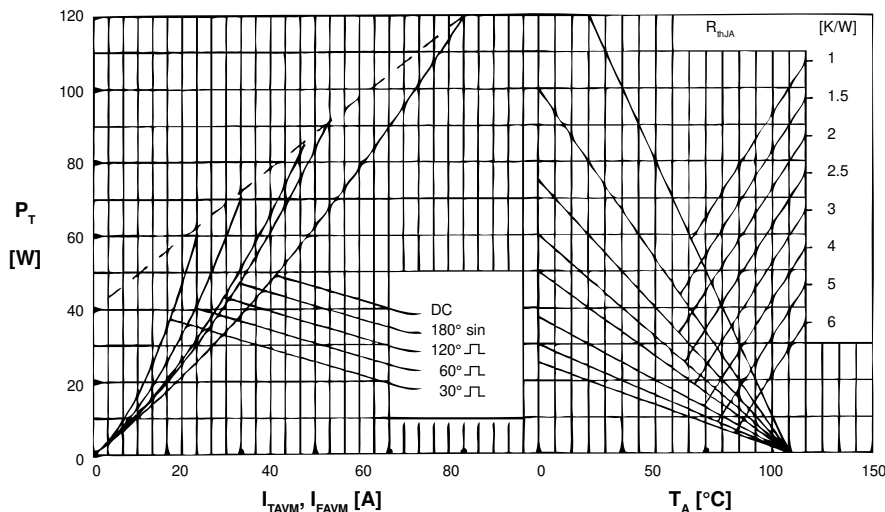


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per diode)

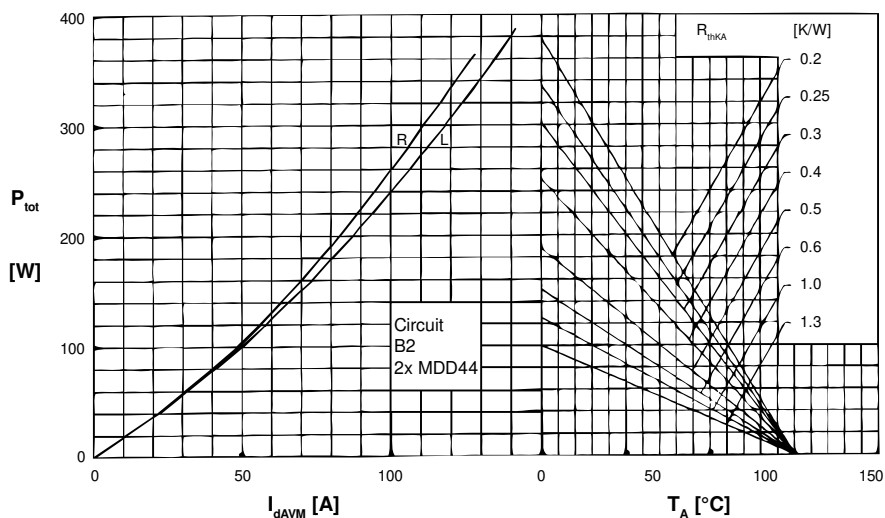


Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load

Rectifier

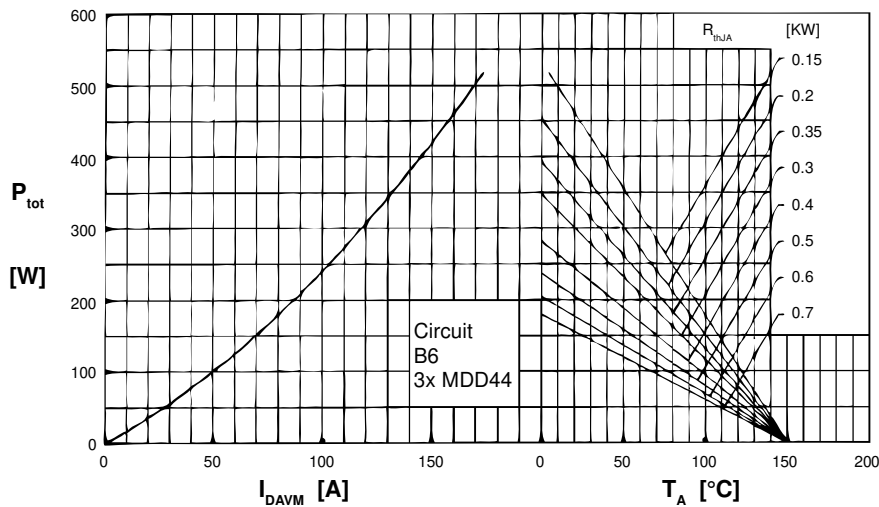


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

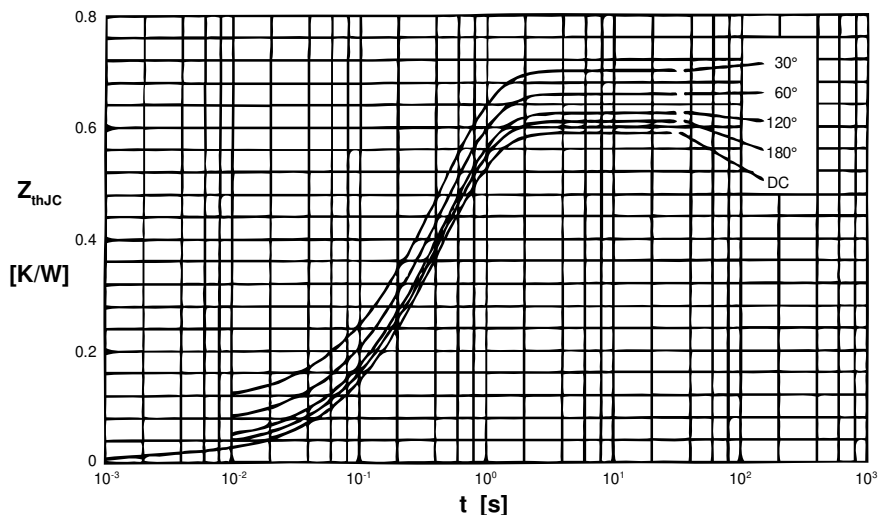


Fig. 7 Transient thermal impedance junction to case (per diode)

$R_{\theta JC}$ for various conduction angles d:

d	$R_{\theta JC}$ [K/W]
DC	0.59
180°	0.61
120°	0.63
60°	0.66
30°	0.70

Constants for $Z_{\theta JC}$ calculation:

i	$R_{\theta i}$ [K/W]	t_i [s]
1	0.012	0.0012
2	0.045	0.0950
3	0.533	0.4550

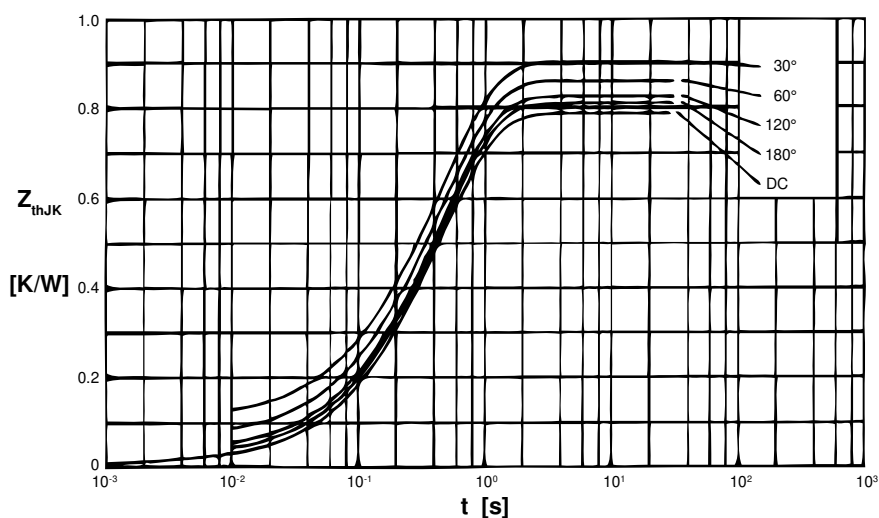


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

$R_{\theta JK}$ for various conduction angles d:

d	$R_{\theta JK}$ [K/W]
DC	0.79
180°	0.81
120°	0.83
60°	0.86
30°	0.90

Constants for $Z_{\theta JK}$ calculation:

i	$R_{\theta i}$ [K/W]	t_i [s]
1	0.012	0.0012
2	0.045	0.0950
3	0.533	0.4550
4	0.200	0.4950